Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3428	"248.1", "255.39", "255.393", "255. 394", "255"".""23".ccls.	USPAT	OR	ON	2007/10/16 11:03
L2	415	427/248.1,255.39,255.393,255.394, 255.23.ccls. and silicon near nitride	USPAT	OR	ON	2007/10/16 11:04
S1	975	427/248.1,255.28,255.39,255.393, 255.394.ccls. and (silicon near nitride SiN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 11:09
S2	. 1	427/248.1,255.28,255.39,255.393, 255.394.ccls. and (silicon near nitride SiN) and (silicon with nitrogen with organic near solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 12:52
S3		427/248.1,255.28,255.39,255.393, 255.394.ccls. and (silicon near nitride SiN) and (silicon with organic near solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:18
S4	. 32	(silicon near nitride SiN) and (silicon with nitrogen with organic near solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/10/03 12:52
S5	8	("0367745"   "0677317"   "5249554"   "6060406"   "6563182"     "6566147").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/03 12:54
S6	1	("6780476").URPN.	USPAT.	OR	ON	2007/10/03 12:55
S7	. 2	427/248.1,255.28,255.39,255.393, 255.394.ccls. and (silicon near nitride SiN) and (nitrogen with organic near solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:48

S8	5	427/248.1,255.28,255.39,255.393, 255.394.ccls. and (silicon near nitride SiN) and (nitrogen same organic near solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:01
S9	0	("2005/0163927").URPN.	USPAT	OR	ON	2007/10/03 13:04
S10	· 7	"427"/\$.ccls. and (silicon near nitride SiN) and (silicon with organic near solvent) same nitrogen	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:21
S11	37	"427"/\$.ccls. and (silicon near nitride SiN) and (silicon with solvent) same nitrogen	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:34
S12	2	"7125582".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:32
S13	143	"427"/\$.ccls. and (silicon near nitride SiN) and ( nitrogen with solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:35
S14	78	"427"/\$.ccls. and (silicon near nitride SiN) and (nitrogen with solvent) and vapor near deposition	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:37
S15		427/248.1,255.28,255.39,255.393, 255.394.ccls. and (silicon near nitride SiN) and (nitrogen with solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:35

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S16	. 4	"427"/\$.ccls. and (silicon near nitride SiN) and (hydrazine with solvent) and vapor near deposition	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:39
S17		"427"/\$.ccls. and (silicon near nitride SiN) and (hydrazine with solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:44
S18		"427"/\$.ccls. and (silicon near nitride SiN) and (hydrazine same solvent) and vapor near deposition	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:39
S19	16	"427"/\$.ccls. and (silicon near nitride SiN "si.sub.2n.sub.4") and (hydrazine with solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:44
S20	16	"427"/\$.ccls. and (silicon near nitride SiN "si.sub.3n.sub.4") and ( hydrazine with solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/10/03 13:45
S21	35	(silicon near nitride SiN "si.sub.3n. sub.4") and (hydrazine with solvent) and vapor near deposition	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OŅ	2007/10/03 13:47
S22	.10	nitride and (hydrazine with organic near solvent) and vapor near deposition	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:48

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S23	. 1	427/248.1,255.28,255.39,255.393, 255.394.ccls. and (hydrazine with organic near solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:48
S24	<b>10</b>	427/248.1,255.28,255.39,255.393, 255.394.ccls. and (nitrogen with organic near solvent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:50
S25		(nitrogen with organic near solvent) and direct near liquid near inject\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:51
S26	15	(nitrogen near (precursor source gas\$4) same solvent) and direct near liquid near inject\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:52
S27	26	(nitrogen near (precursor source gas\$4) same (solution solvent)) and direct near liquid near inject\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:51
S28	1217	(nitrogen near (precursor source gas\$4) same solvent) and nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:52
S29	610	(nitrogen near (precursor source gas\$4) same solvent) and nitride with (film coat\$4 layer deposit\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:54

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S30	140	(nitrogen near (precursor source gas\$4) with solvent) and nitride with (film coat\$4 layer deposit\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2007/10/03 13:54
S31	10	(nitrogen near (precursor source gas\$4) with solvent) and nitride with (film coat\$4 layer deposit\$4) and hydrazine	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/03 13:54
S32	63	(silicon near nitride "si.sub.3n.sub. 4") with (coat\$4 layer film deposit\$4) and ((precursor reactant) with solvent with liquid) and "427"/\$.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 13:37
S33	8	("0367745"   "0677317"   "5249554"   "6060406"   "6563182"   "6566147").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/04 10:36
S34		"5393564".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 10:53
S35 .	2	("4906493"   "4993361").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/10/04 10:54
·S36	⋅31	("4993361").URPN.	USPAT	OR	ON	2007/10/04 10:55
S37	30	("5393564").URPN.	USPAT	OR	ON	2007/10/04 10:57
S40	0	(silicon near nitride "si.sub.3n.sub. 4") with (coat\$4 layer film deposit\$4) and ((precursor reactant) with solvent with liquid) and (dimethylhydrazine DMH)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:11
S41	2	(silicon near nitride "si.sub.3n.sub. 4") with (coat\$4 layer film deposit\$4) and ((precursor reactant) with solvent with liquid) and (dimethylhydrazine dimethyl adj hydrazine DMH)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:14

S42	2	(silicon near nitride "si.sub.3n.sub. 4") and ((precursor reactant) with solvent with liquid) and (dimethylhydrazine dimethyl adj hydrazine DMH)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:28
S43		"11096057"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:28
S44	1	"11/096057"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:29
S45 .	0	10*631627	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:29
S46	3	10/631627	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/10/04 11:31
S47	. 2	"6277200".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:31
S48		(silicon near nitride "si.sub.3n.sub. 4") and ((precursor reactant) with solvent with liquid) and "427"/255. 394.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:48

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S49	23	(McSwiney Mcwilliams).in. and (silicon near nitride "si.sub.3n.sub.4")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:49
S50	12	(McSwiney Mcwilliams).in. and (silicon near nitride "si.sub.3n.sub. 4") and solvent	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:51
S51	2	(McSwiney Mcwilliams).in. and (silicon near nitride "si.sub.3n.sub.4") and solvent and silazane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 11:52
S52	165	direct near liquid near inject\$4 and solvent with (precursor reactant)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 13:37
S53	141	direct near liquid near inject\$4 and solvent with (precursor reactant) and silicon and nitrogen	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 13:39
S54.	631645 ·	ce	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 13:38
S55	146	direct near liquid near inject\$4 and solvent with (precursor reactant source) and silicon and nitrogen	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 13:38

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S56	115	direct near liquid near inject\$4 and solvent with (precursor reactant) and silicon and nitrogen and nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/04 13:42
S57	62	direct near liquid near inject\$4 and organic near solvent with (precursor reactant) and silicon and nitrogen and nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/05 12:06
S58	0	("2005/0145177").URPN.	USPAT	OR	ON	2007/10/04 13:45
S72		"6567246".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/05 15:15
S73	2	"5923504".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/05 15:16